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PATENT ABSTRACTS OF JAPAN

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(71) Applicant: **NEC CORP**(72) Inventor: **MASUOKA SADA AKI**

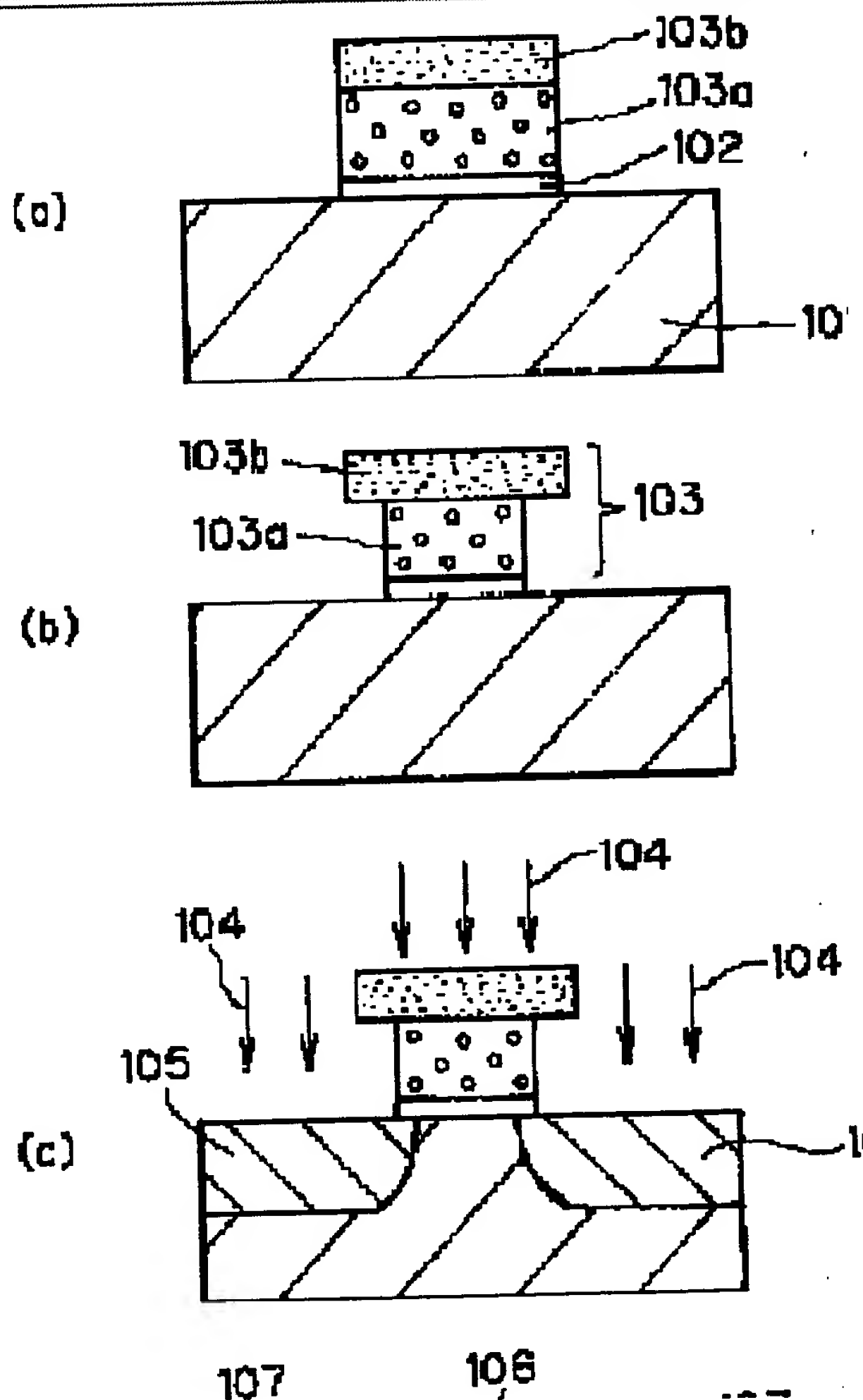
(74) Representative:

(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

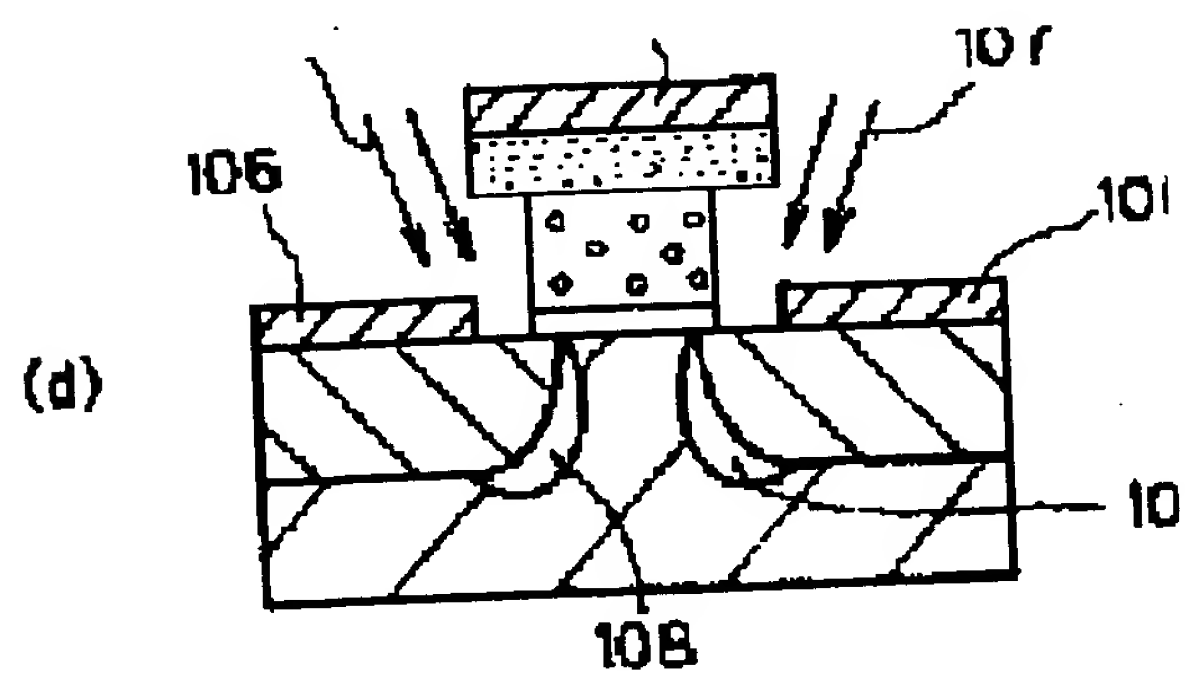
(57) Abstract:

PROBLEM TO BE SOLVED: To suppress leakage by suppressing the short channel effect, preventing a punch through, and sufficiently repairing a defect in a pocket region introduced at ion implantation.

SOLUTION: A gate insulation film 102, a polysilicon film 103a and a WSi film 103b are formed on a p-type silicon substrate 101, to pattern into a gate electrode shape. Then, a polysilicon film 103a is side-etched to form a T-shaped gate electrode 103, and then As⁺ 104 is implanted to form a source/drain region 105. Then a Ti film 106 is accumulated in a collimate sputtering process, etc., and BF₂⁺ is implanted obliquely to form a pocket region 108. After this, the Ti film 106 is removed, and high-temperature heat treatment is performed, to repair a defect introduced by activation of implanted ionic species and ion implantation.



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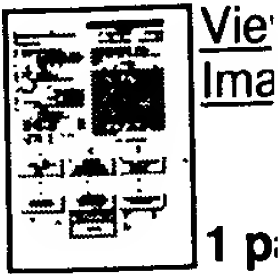
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April 17, 1997 JP1997000100094

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How 2 known family members

- Family:
- Forward References:
- Other Abstract Info:

PDF	Patent	Pub.Date	Inventor	Assignee	Title
	US6281052	2001-08-28	Shinmura; Toshiki	NEC Corporation	Method of manufactur semiconductor device

None

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